

General Description

- AEC-Q101 Qualified
- Trench Power MOSFET - AlphaSGT™ technology
- Combined of low $R_{DS(ON)}$ and wide safe operating area (SOA)
- Higher in-rush current enabled for faster start-up and shorter down time
- RoHS 2.0 and Halogen-Free Compliant

Applications

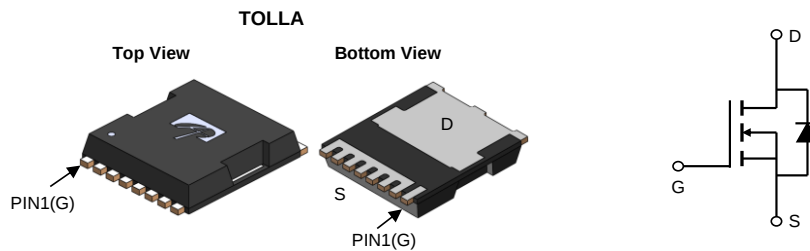
- Load switch
- BMS
- Motor

Product Summary

V_{DS}	150V
I_D (at $V_{GS}=10V$)	206A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 4.7mΩ
$R_{DS(ON)}$ (at $V_{GS}=8V$)	< 5.3mΩ

100% UIS Tested
100% Rg Tested

Max $T_j=175^{\circ}C$



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOTL66518Q	TOLLA	Tape & Reel	2000

Absolute Maximum Ratings $T_A=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	206	A
$T_C=25^{\circ}C$		145	
$T_C=100^{\circ}C$			
Pulsed Drain Current ^C ($\leq 100\mu s$)	I_{DM}	824	
Continuous Drain Current	I_{DSM}	29	A
$T_A=25^{\circ}C$		24	
$T_A=70^{\circ}C$			
Avalanche Current ^C	I_{AS}	70	A
Avalanche energy $L=0.3mH$ ^C	E_{AS}	735	mJ
Diode reverse recovery $V_{DS}=0$ to 75V, $I_F \leq 300A$, $T_J \leq 125^{\circ}C$	di/dt	500	A/us
Power Dissipation ^B	P_D	500	W
$T_C=25^{\circ}C$		250	
$T_C=100^{\circ}C$			
Power Dissipation ^A	P_{DSM}	10	W
$T_A=25^{\circ}C$		7	
$T_A=70^{\circ}C$			
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	10	15	$^{\circ}C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient ^{A D}	$R_{\theta JA}$	35	45	$^{\circ}C/W$
Steady-State				
Maximum Junction-to-Case	$R_{\theta JC}$	0.2	0.3	$^{\circ}C/W$
Steady-State				

Electrical Characteristics (T_j=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	150			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =150V, V _{GS} =0V T _j =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.7	3.2	3.7	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =100A T _j =175°C		3.9	4.7	mΩ
		V _{GS} =8V, I _D =75A		4.2	5.3	mΩ
				9.7	12	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		50		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.68	1	V
I _S	Maximum Body-Diode Continuous Current				200	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =75V, f=1MHz		6460		pF
C _{oss}	Output Capacitance			820		pF
C _{rss}	Reverse Transfer Capacitance			5		pF
R _g	Gate resistance	f=1MHz	1.1	2.3	3.5	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =75V, I _D =20A		80	115	nC
Q _{gs}	Gate Source Charge			32		nC
Q _{gd}	Gate Drain Charge			15		nC
Q _{oss}	Output Charge	V _{GS} =0V, V _{DS} =75V		273		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =75V, R _L =3.75Ω, R _{GEN} =3Ω		27		ns
t _r	Turn-On Rise Time			20		ns
t _{D(off)}	Turn-Off DelayTime			49		ns
t _f	Turn-Off Fall Time			28		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		86		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		920		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 175° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.

B. The power dissipation P_D is based on T_{j(MAX)}=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{j(MAX)}=175° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{j(MAX)}=175° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

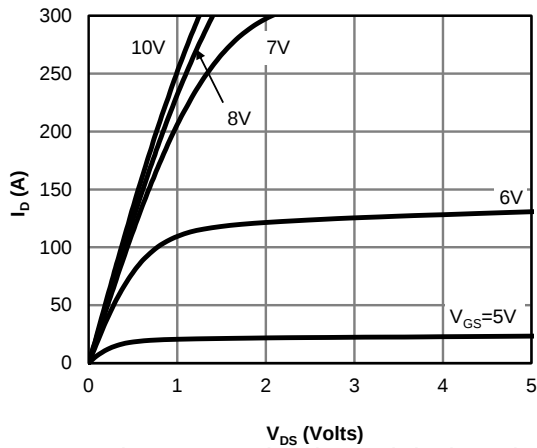


Figure 1: On-Region Characteristics (Note E)

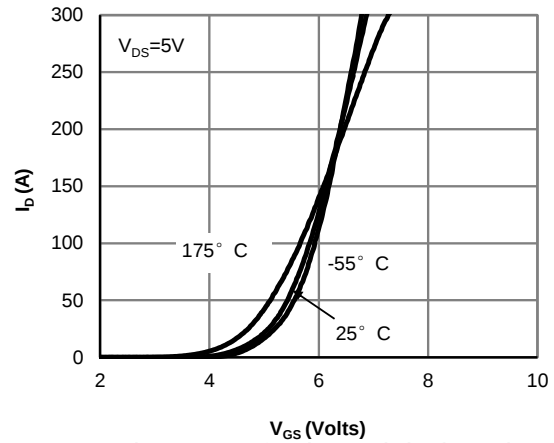


Figure 2: Transfer Characteristics (Note E)

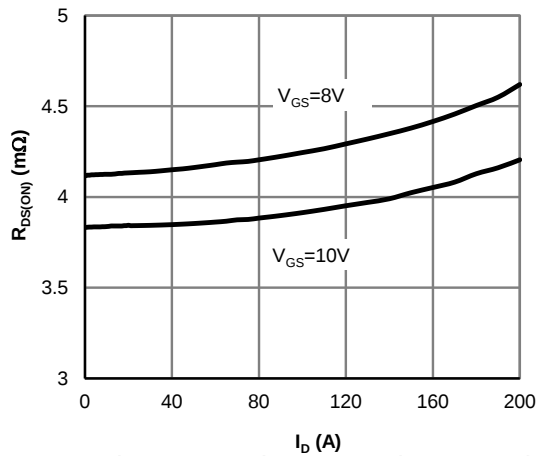


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

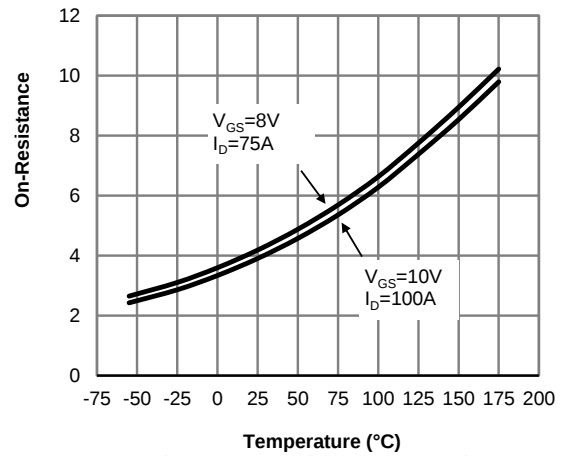


Figure 4: On-Resistance vs. Junction Temperature (Note E)

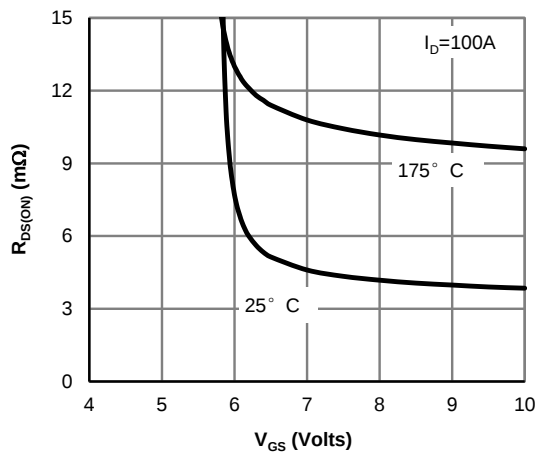


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

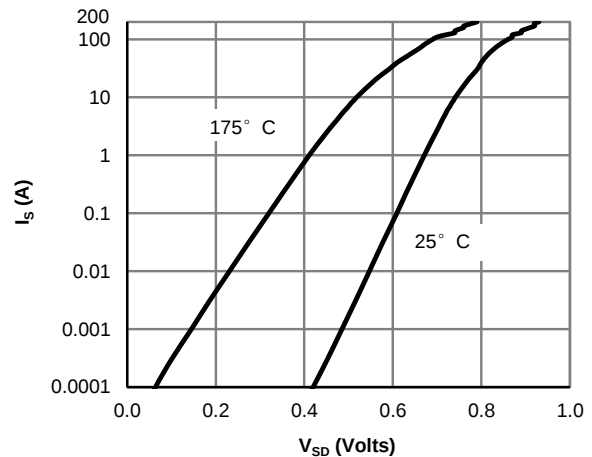
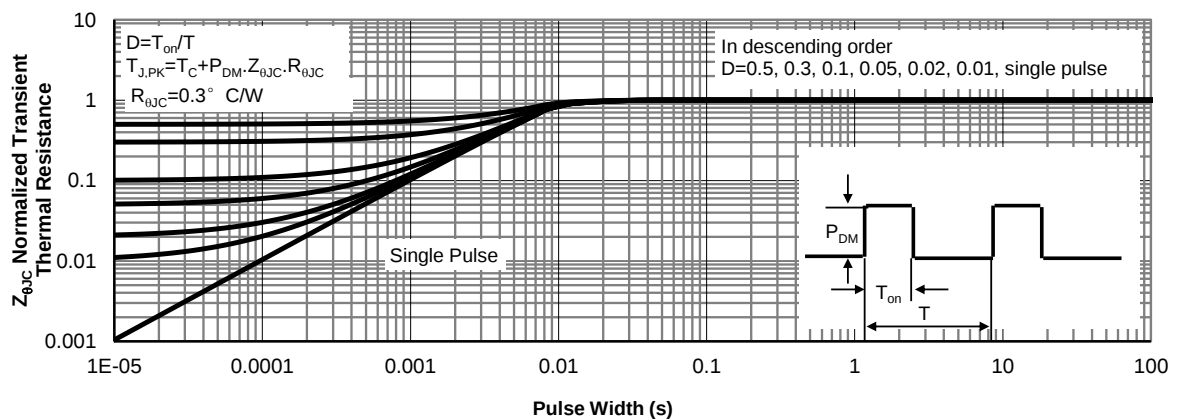
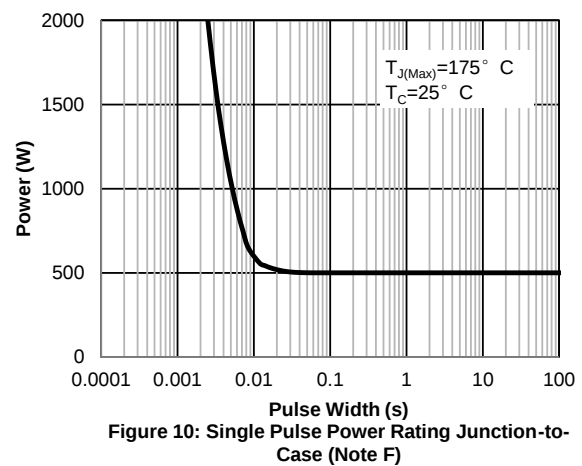
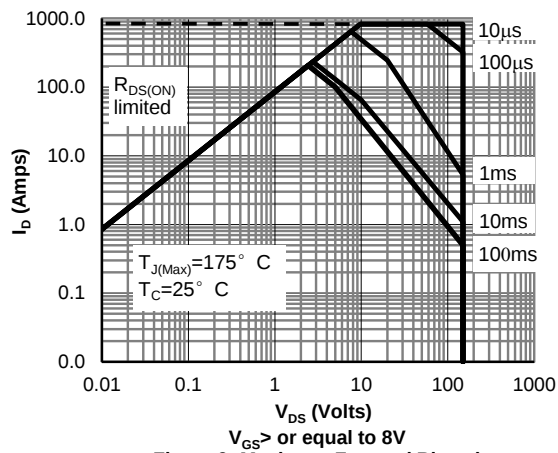
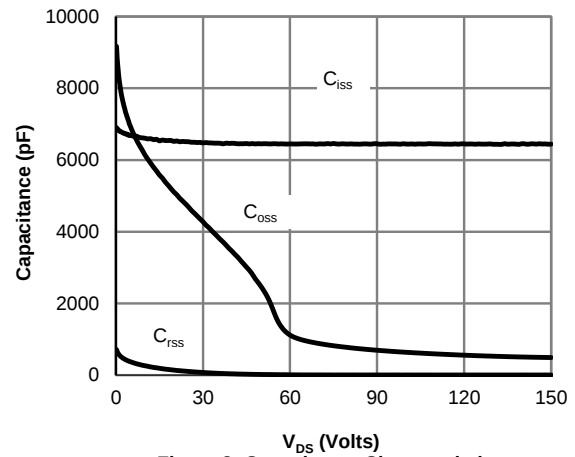
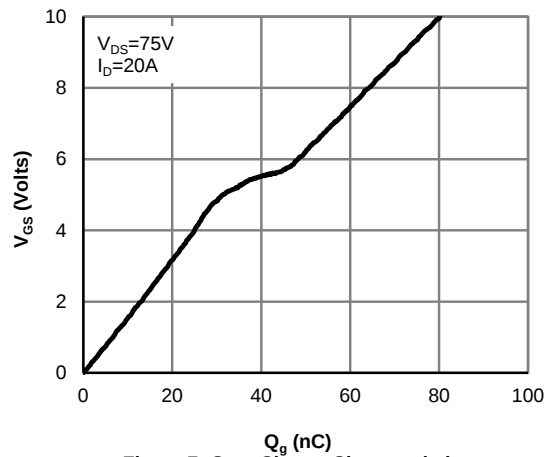
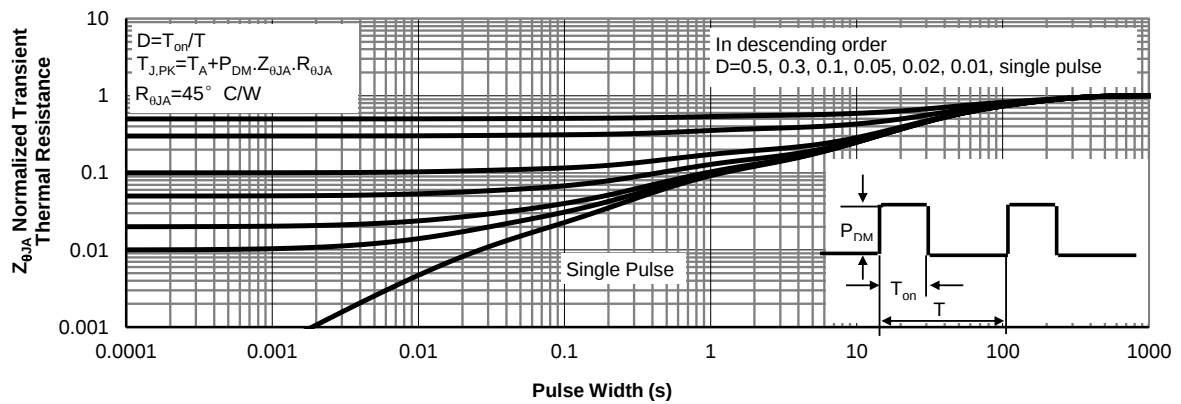
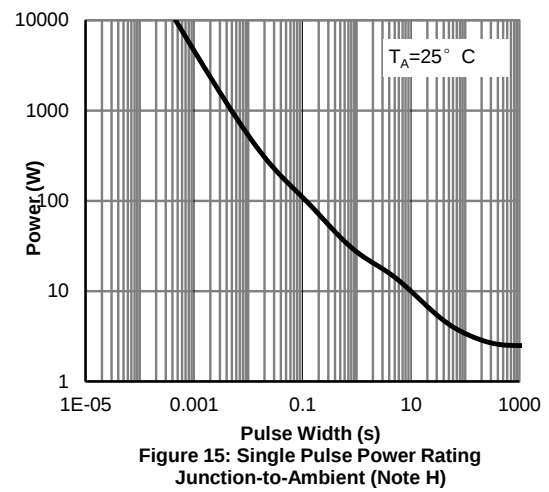
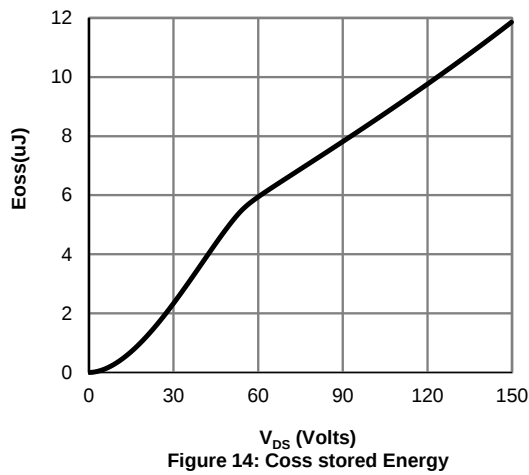
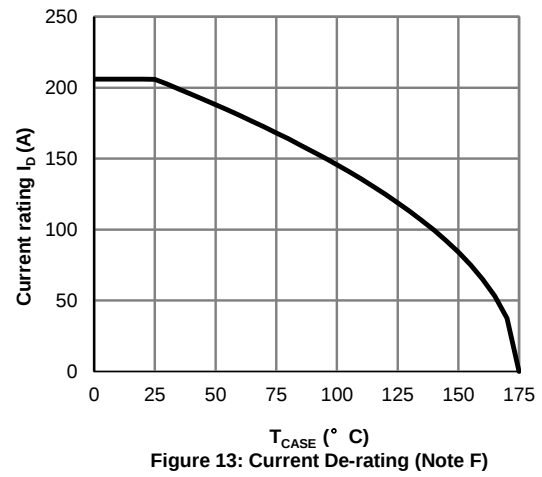
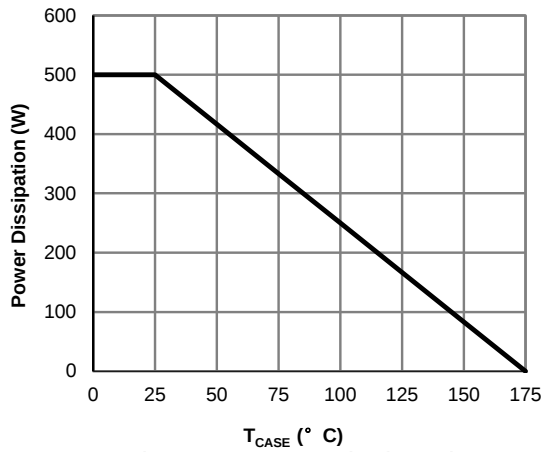


Figure 6: Body-Diode Characteristics (Note E)

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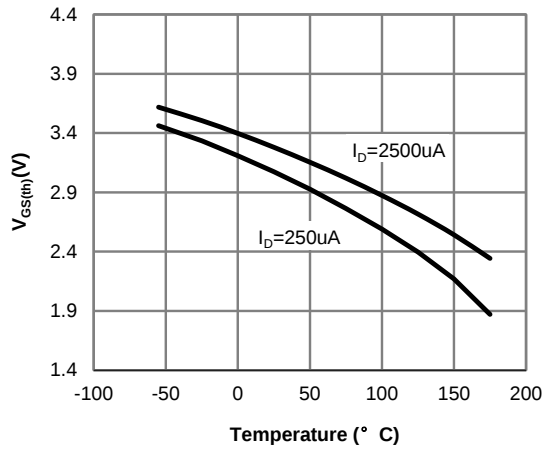


Figure 17: $E_{GS(th)}$ vs Junction Temperature

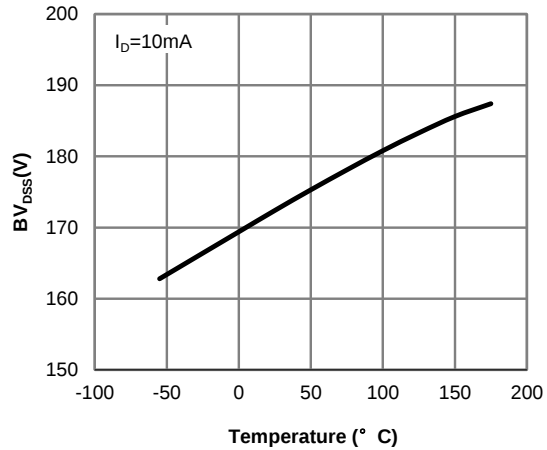


Figure 18: Drain-source breakdown voltage vs. Junction Temperature

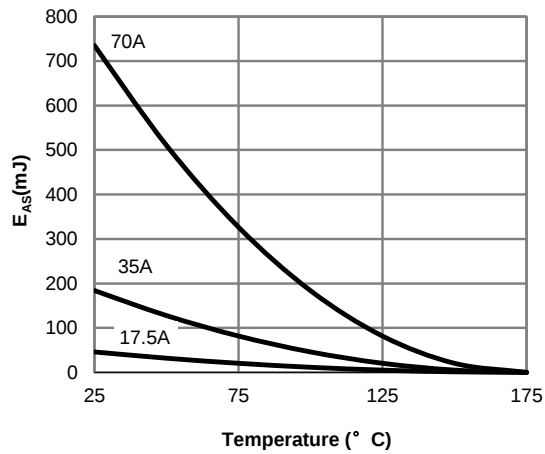


Figure 19: E_{AS} vs. Junction Temperature

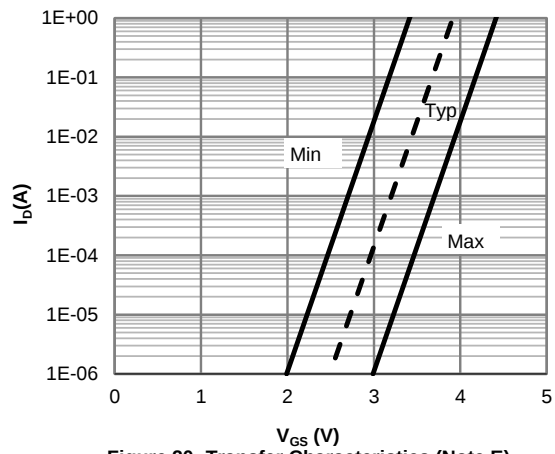


Figure 20: Transfer Characteristics (Note E)

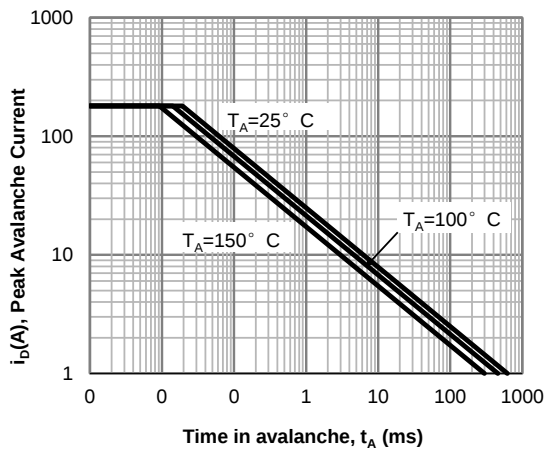


Figure 21: Single Pulse Avalanche capability

Figure A: Gate Charge Test Circuit & Waveforms

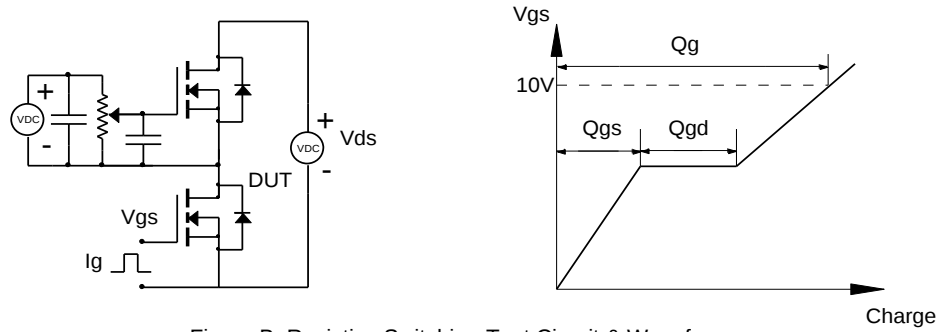


Figure B: Resistive Switching Test Circuit & Waveforms

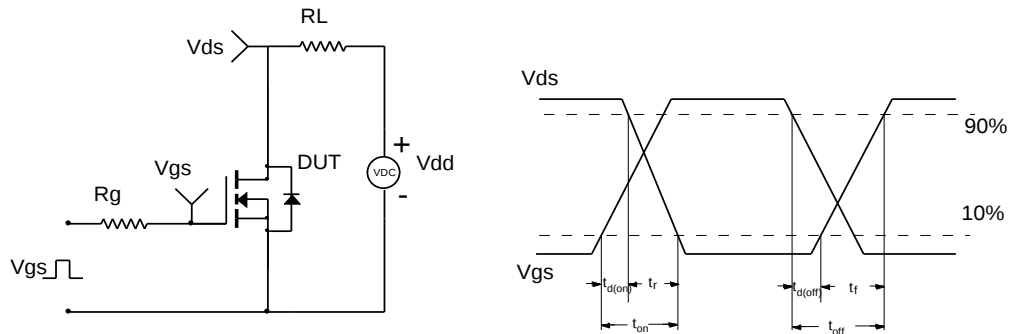


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

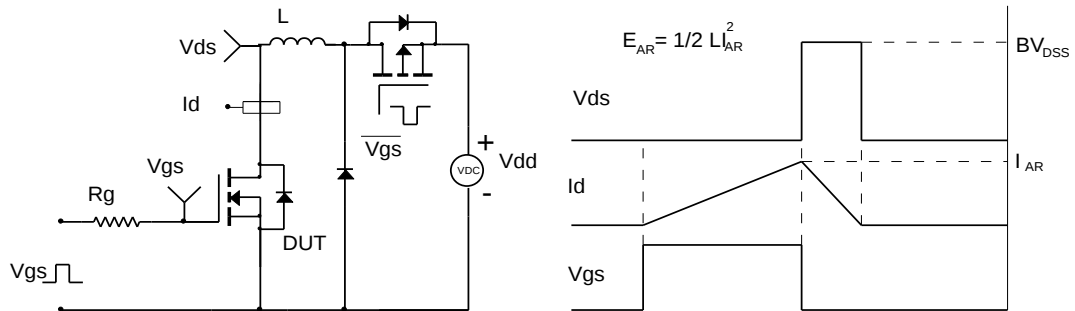


Figure D: Diode Recovery Test Circuit & Waveforms

